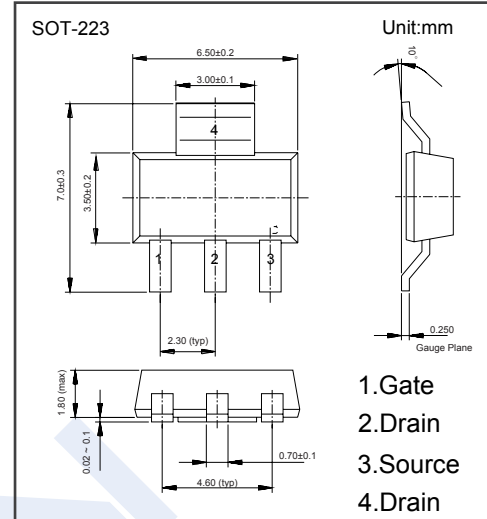
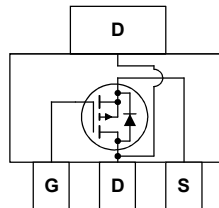


P-Channel MOSFET

NDT2955 (KDT2955)

■ Features

- $V_{DS} (V) = -60V$
- $I_D = -2.5 A$ ($V_{GS} = -10V$)
- $R_{DS(ON)} < 300m\Omega$ ($V_{GS} = -10V$)
- $R_{DS(ON)} < 500m\Omega$ ($V_{GS} = -4.5V$)



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current (Note.1)	I_D	-2.5	A
Pulsed Drain Current	I_{DM}	-15	
(Note.1)	P_D	3	W
Power Dissipation (Note.2)		1.3	
(Note.3)		1.1	
Thermal Resistance.Junction- to-Ambient (Note.1)	R_{thJA}	42	$^\circ C/W$
Thermal Resistance.Junction- to-Case	R_{thJC}	12	
Junction Temperature	T_J	150	$^\circ C$
Junction Storage Temperature Range	T_{stg}	-55 to 150	

Note.1: $42^\circ C/W$ when mounted on a $1in^2$ pad of 2 oz copper

Note.2: $95^\circ C/W$ when mounted on a $.0066in^2$ pad of 2 oz copper

Note.3: $110^\circ C/W$ when mounted on a minimum pad.

P-Channel MOSFET

NDT2955 (KDT2955)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	I _D =-250 μA, V _{GS} =0V		-60		V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V, V _{GS} =0V			-10	μA
Gate-Body leakage current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} I _D =-250 μA	-2		-4	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-2.5A			300	mΩ
		V _{GS} =-4.5V, I _D =-2A			500	
		V _{GS} =-10V, I _D =-2.5A T _J =125°C			513	
On state drain current	I _{D(ON)}	V _{GS} =-10V, V _{DS} =-5V	-12			A
Forward Transconductance	g _{FS}	V _{DS} =-10V, I _D =-2.5A		5.5		S
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =-30V, f=1MHz		601		pF
Output Capacitance	C _{oss}			85		
Reverse Transfer Capacitance	C _{rss}			35		
Total Gate Charge	Q _g	V _{GS} =-10V, V _{DS} =-30V, I _D =-2.5A (Note.1)		11	15	nC
Gate Source Charge	Q _{gs}			2.4		
Gate Drain Charge	Q _{gd}			2.7		
Turn-On DelayTime	t _{d(on)}	V _{GS} =-10V, V _{DS} =-30V, I _D =-1A, R _G =6 Ω (Note.1)		12	21	ns
Turn-On Rise Time	t _r			10	20	
Turn-Off DelayTime	t _{d(off)}			19	34	
Turn-Off Fall Time	t _f			6	12	
Body Diode Reverse Recovery Time	t _{rr}	I _F =-2.5A, di/dt=100A/μs		25		nC
Body Diode Reverse Recovery Charge	Q _{rr}			40		
Drain-Source Avalanche Energy	W _{DSS}	Single Pulse, V _{DD} = 30 V, I _D = 2.5 A			174	mJ
Maximum Body-Diode Continuous Current	I _S				-2.5	A
Diode Forward Voltage	V _{SD}	I _S =-2.5A, V _{GS} =0V (Note.1)			-1.2	V

Note.1: Pulse Test: Pulse Width < 300μs, Duty Cycle < 2.0%

■ Marking

Marking	*DT2955
---------	---------

P-Channel MOSFET

NDT2955 (KDT2955)

■ Typical Characteristics

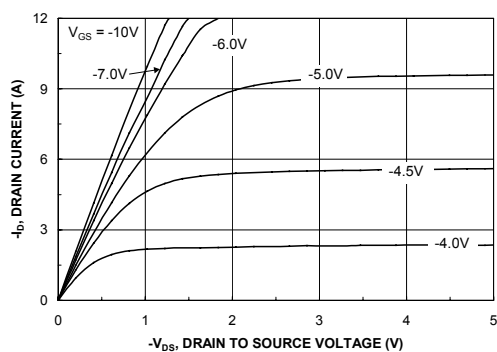


Figure 1. On-Region Characteristics.

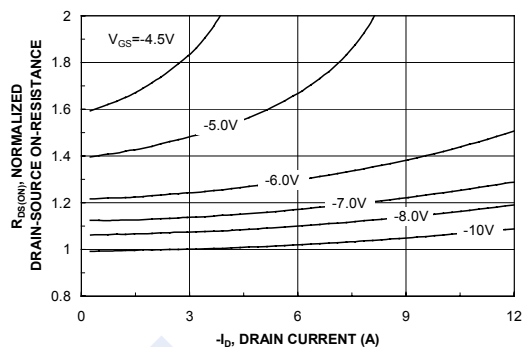


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

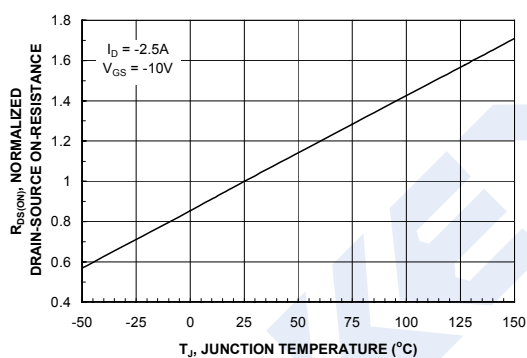


Figure 3. On-Resistance Variation with Temperature.

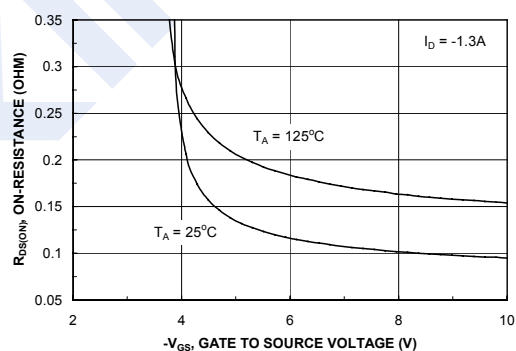


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

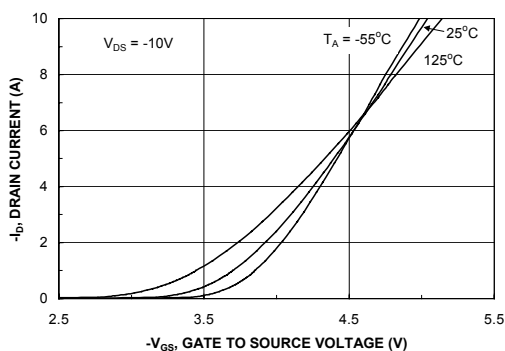


Figure 5. Transfer Characteristics.

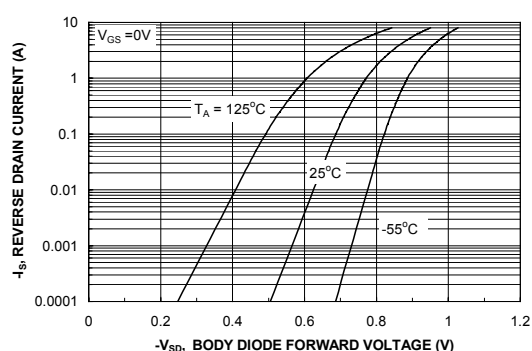


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

P-Channel MOSFET

NDT2955 (KDT2955)

■ Typical Characteristics

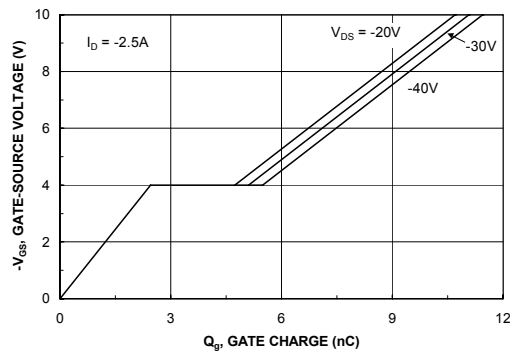


Figure 7. Gate Charge Characteristics.

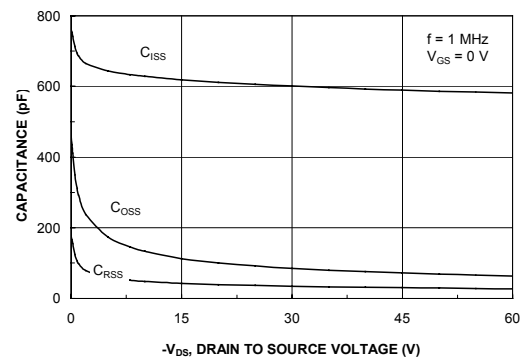


Figure 8. Capacitance Characteristics.

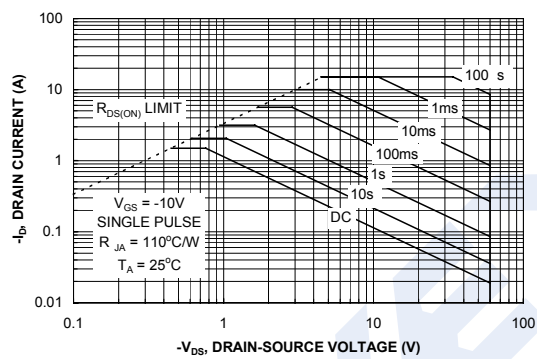


Figure 9. Maximum Safe Operating Area.

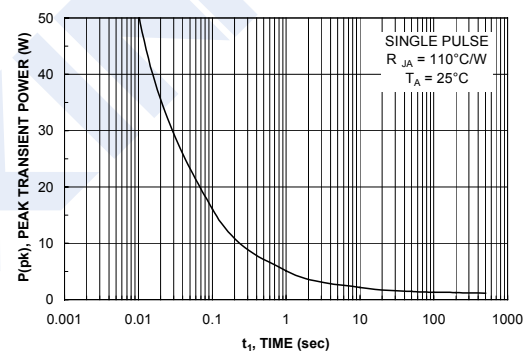


Figure 10. Single Pulse Maximum Power Dissipation.

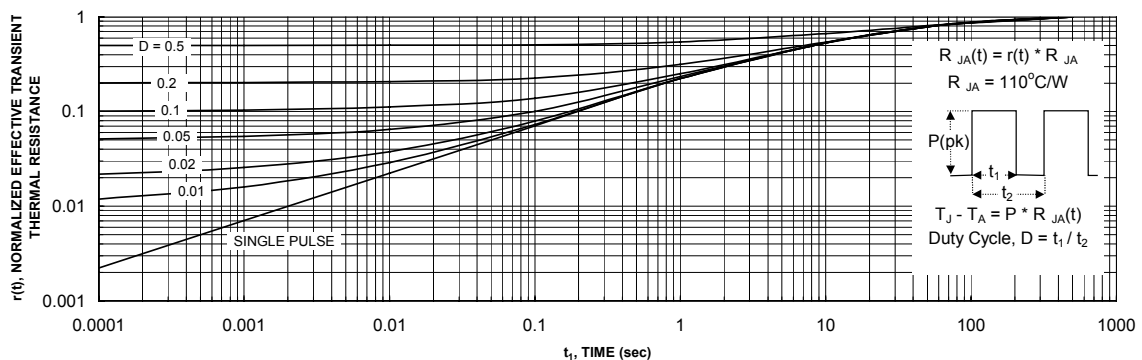


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c.
Transient thermal response will change depending on the circuit board design.